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SNS COLLEGE OF TECHNOLOGY

(An Autonomous Institution) COIMBATORE-35 Accredited by NBA-AICTE and Accredited by NAAC – UGC with A+ Grade Approved by AICTE, New Delhi & Affiliated to Anna University, Chennai



DEPARTMENT OF ELECTRICAL AND ELECTRONICS ENGINEERING

19EET202 / ANALOG ELECTRONICS II YEAR / III SEMESTER









TOPIC OUTLINE





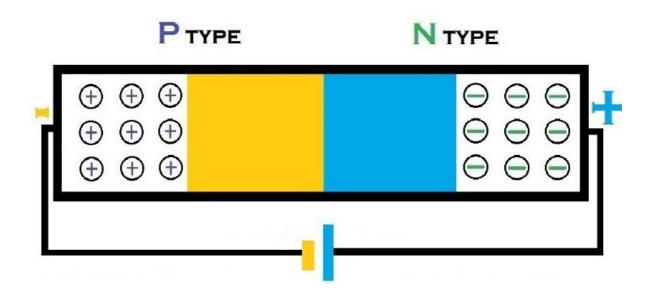
- ✓ Introduction
- ✓ Diodes
- ✓ PN Junctions
- \checkmark Forward bias
- \checkmark Reverse bias
- ✓ VI characteristics



PN JUNCTION



PN-junction: When P-type semiconductor is suitably joined to N-type semiconductor, the contact surface is called PN-junction.

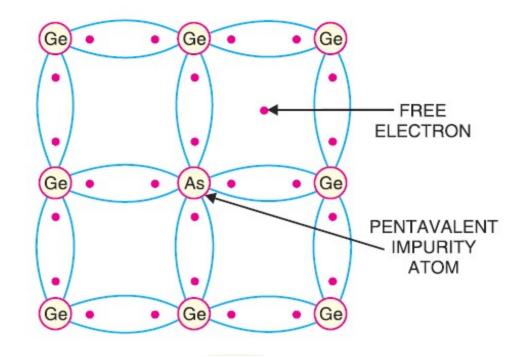




N-TYPE SEMICONDUCTOR



N-Type: When a small amount of pentavalent impurity is added to a pure semiconductor, it's known as a N-type semiconductor.

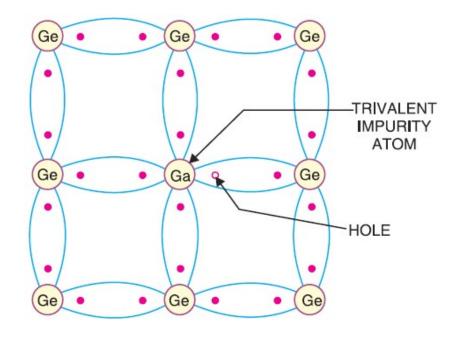




P-TYPE SEMICONDUCTOR



P-type: when a small amount of trivalent impurity is added to a pure semiconductonit's called P-type semiconductor.





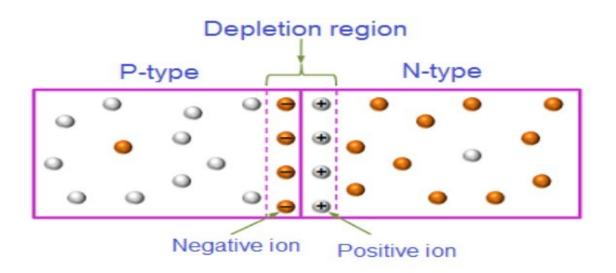




DEPLETION REGION



The depletion region, also called depletion layer, depletion zone. The combining o electrons and holes depletes the holes in the P-region and the electrons in the N-region near the junction.







BIASING A PN-JUNCTION



In relation to a PN junction, there are two bias condition

Biasing a PN-junction

Forward biasing

Reverse biasing



BATTERY CONNECTION



□ Forward Bias Mode: Positive terminal connected to P-region and negative terminal connected to N-region.

Reverse bias mode: Negative terminal connected to P-region and positive terminal connected to N-region.

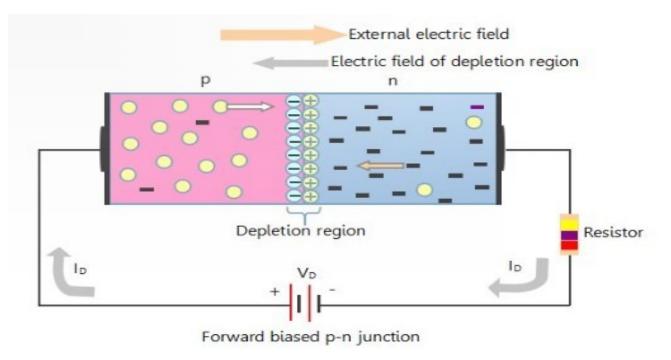




FORWARD BIASING



• When voltage is applied across a diode in such a way that the diode allows current and the potential barrier reduced, the diode is said to be forward-biased.

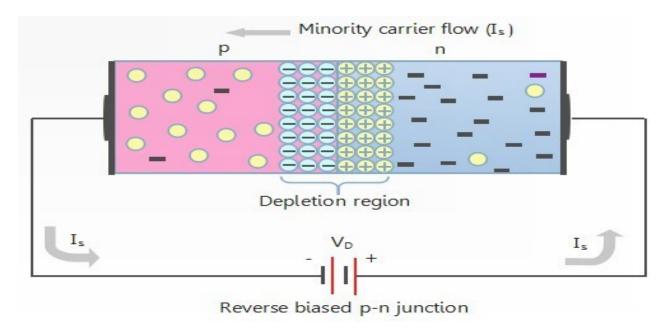




REVERSE BIASING



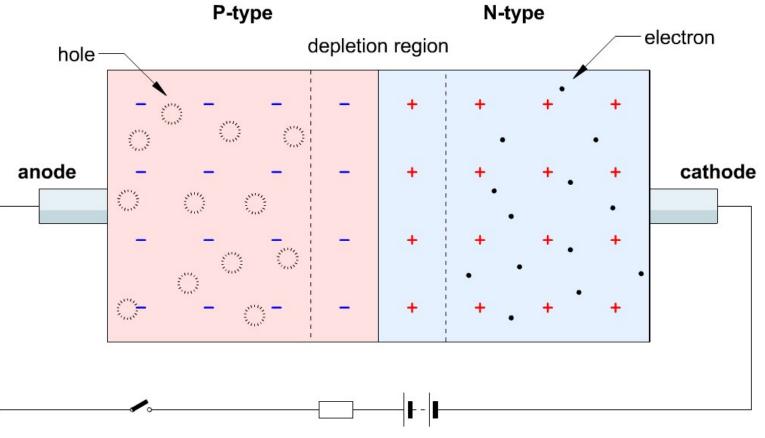
When voltage is applied across a diode in such a way that the diode prohibits curre and potential barrier increase, the diode is said to be reverse-biased.





ANIMATION



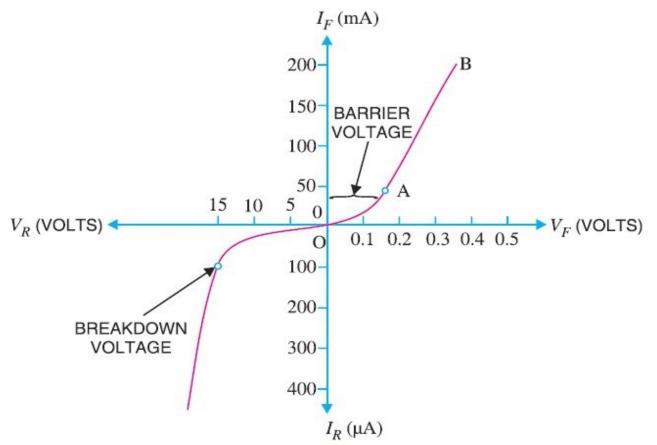


https://www.youtube.com/watch?v=OyC02DWq3ml



V-I CHARACTERISTICS OF PN-JUNCTION





The curve drawn between voltage across the junction along x axis and current through the y axis.



IN FORWARD BIAS



- □ No current flows until the barrier voltage (0.3 for Ge) is overcome.
- Then the curve has linear rise and the current increase with the increase forward voltage.
- Above the 3v, the majority carriers passing the junction gain sufficient energy to kno out the electrons.
- Therefore, the forward current increase sharply.





IN REVERSE BIAS



Junction resistance, potential barrier increase.

- When reverse voltage is increased beyond a value, called breakdown voltage.
- Reverse current increase sharply.
- Above 25 reverse voltage, destroys the junction permanently.





Contd..



Maximum Forward Current – It is the highest instantaneous current under forve bias Condition that can flow through the junction.

Peak Inverse Voltage – It is the maximum reverse voltage that can be applied to PN junction.

Maximum Power Rating – Maximum power that can be dissipated at the junction without Damaging the junction.





Assessment



Which among the following is the most commonly used semiconductor?

- Silicon
- Carbon
- Germanium
- Sulphur

A semiconductor has generally valence electrons.

- 2
- 3
- 6
- 4

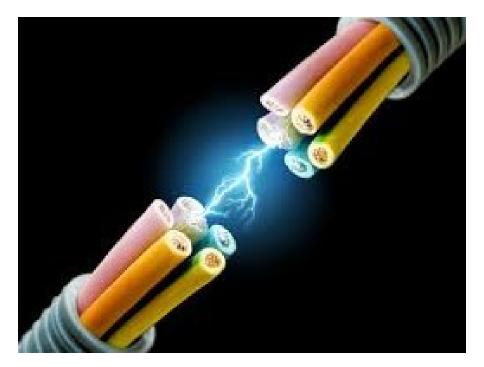












...THANK YOU